AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A semiconductor manufacturing apparatus comprising:

~~at least two chambers for processing a first part of an object by a first plasma treatment under atmospheric pressure or approximate to atmospheric pressure in a first one of the two chambers and for processing a second part of the object by a second plasma treatment under atmospheric pressure or approximate to atmospheric pressure in a second one of the two chambers simultaneously with the first plasma treatment;~~

a ~~first~~ plasma generating device for ~~performing the first~~ generating a plasma ~~treatment in the first one of the two chambers;~~ ~~and~~

~~a second plasma generating device for performing the second plasma treatment in the second one of the two chambers;~~

a first chamber for performing a plasma treatment on an object by the plasma therein under atmospheric pressure or approximate to atmospheric pressure; and

an ink-jet device for applying a droplet to the object,

wherein the plasma generating device is provided in the first chamber,

wherein the ink-jet device is provided in a second chamber; and

wherein the object is transferred in the ~~two chambers~~ first chamber along a first direction and the ~~first~~ plasma generating device ~~and the second plasma generating device are~~ is moved in the first chamber along a second direction intersecting with the first direction.

2. (Canceled)

3. (Previously Presented) A semiconductor manufacturing apparatus according to claim 1, wherein the first direction is a unidirection.

4. (Previously Presented) A semiconductor manufacturing apparatus according to claim 1, wherein the object is transferred continuously or with the use of step-feed.

5. (Withdrawn) A semiconductor manufacturing apparatus comprising a means for transferring an object to be processed, a plurality of plasma generating means for performing film formation treatment, etching treatment or ashing treatment,

wherein the plurality of plasma generating means are arranged in the intersecting direction with a transferring direction of the object to be processed, and

wherein film formation treatment, etching treatment or ashing treatment is performed on the object to be processed by transferring of the object to be processed and generating plasma in at least one of the plurality of plasma generating means.

6. (Withdrawn) A semiconductor manufacturing apparatus according to claim 5, wherein the plasma generating means has a structure which is performed under atmospheric pressure or approximate to atmospheric pressure.

7. (Withdrawn) A semiconductor manufacturing apparatus according to claim 5, wherein the means for transferring the object to be processed has a structure to transfer the object to be processed unidirectionally.

8. (Withdrawn) A semiconductor manufacturing apparatus according to claim 5, wherein the means for transferring the object to be processed has a structure to perform continuous or step-feed.

9. (Currently Amended) A semiconductor manufacturing apparatus comprising:

~~at least two chambers for processing a first part of an object by a first plasma treatment under atmospheric pressure or approximate to atmospheric pressure in a first one of the two chambers and for processing a second part of the object by a second plasma treatment under atmospheric pressure or approximate to atmospheric pressure in a second one of the two chambers simultaneously with the first plasma treatment;~~

a ~~first~~ plasma generating device for ~~performing the first plasma treatment in the first one of the two chambers~~ generating a plasma;

~~a second plasma generating device for performing the second plasma treatment in the second one of the two chambers; and~~

a first chamber for performing a plasma treatment on an object by the plasma therein under atmospheric pressure or approximate to atmospheric pressure; and

an ink-jet device for applying a droplet to the object,

wherein the plasma generating device is provided in the first chamber,

wherein the ink-jet device is provided in a second chamber, and

wherein the object is transferred in the ~~two chambers~~ second chamber along a first direction and the ink-jet device is moved in the second chamber along a second direction intersecting with the first direction.

10. (Previously Presented) A semiconductor manufacturing apparatus according to claim 9, wherein the applying of the droplet is performed to a surface of the object under atmospheric pressure or approximate to atmospheric pressure.

11. (Previously Presented) A semiconductor manufacturing apparatus according to claim 9, wherein the first direction is a unidirection.

12. (Previously Presented) A semiconductor manufacturing apparatus according to claim 9, wherein the object is transferred continuously or with the use of step-feed.

13. (Withdrawn) A semiconductor manufacturing apparatus according to claim 9, wherein the droplet is an organic solvent containing organic resin or metal element.

14. (Withdrawn) A semiconductor manufacturing apparatus comprising a means for transferring an object to be processed, a plurality of droplet spraying means for spraying a droplet onto the surface of the object to be processed,

wherein the plurality of droplet spraying means are arranged in the intersecting direction with a transferring direction of the object to be processed,

and a droplet is attached to the object to be processed by the transfer of the object to be processed and spraying a droplet from at least one of the plurality of droplet spraying means.

15. (Withdrawn) A semiconductor manufacturing apparatus according to claim 14, wherein the droplet is attached under atmospheric pressure or approximate to atmospheric pressure.

16. (Withdrawn) A semiconductor manufacturing apparatus according to claim 14, wherein the means for transferring the object to be processed has a structure to transfer the object to be processed unidirectionally.

17. (Withdrawn) A semiconductor manufacturing apparatus according to claim 14, wherein the means for transferring the object to be processed has a structure to perform continuous or step-feed.

18. (Withdrawn) A semiconductor manufacturing apparatus according to claim 14, wherein the droplet is an organic solvent containing organic resin or a metal element.

19. (Currently Amended) A semiconductor manufacturing apparatus comprising:

at least one plasma generating device for ~~processing an object by a plasma treatment under atmospheric pressure or approximate to atmospheric pressure~~ generating a plasma; ~~and~~

a first chamber for performing a plasma treatment on an object by the plasma therein under atmospheric pressure or approximate to atmospheric pressure; and

at least one ink-jet device for applying a droplet to the object;

wherein the plasma generating device is provided in the first chamber,

wherein the ink-jet device is provided in a second chamber,

wherein the object is transferred in ~~a treatment~~ the first chamber along a first direction and the plasma generating device is moved in the first chamber along a second direction intersecting with the first direction, and

wherein the ink-jet device is moved in the second chamber along a third direction intersecting with the first direction.

20. (Previously Presented) A semiconductor manufacturing apparatus according to claim 19, wherein the plasma treatment is performed by the plasma generating device for forming a film over the object, etching the object or ashing the object.

21. (Previously Presented) A semiconductor manufacturing apparatus according to claim 19, wherein the first direction is a unidirection.

22. (Previously Presented) A semiconductor manufacturing apparatus according to claim 19, wherein the object is transferred continuously or with the use of step-feed.

23. (Previously Presented) A semiconductor manufacturing apparatus according to claim 19, wherein a plurality of treatments selected from the film forming treatment, the etching treatment, the ashing treatment or the applying of the droplet are performed simultaneously.

24. (Withdrawn) A semiconductor manufacturing apparatus comprising a means for transferring an object to be processed, a plurality of plasma generating means for performing film formation treatment, etching treatment or ashing treatment on the object to be processed, a plurality of droplet spraying means for attaching a droplet on the object to be processed,

wherein the plurality of plasma generating means are arranged in the intersecting direction with a transferring direction of the object to be processed,

wherein the plurality of the droplet spraying means are arranged in the intersecting direction with a transferring direction of the object to be processed,

wherein the film formation treatment, the etching treatment or the ashing treatment is performed on the object to be processed by the transfer of the object to be processed and generating plasma in at least one of the plurality of plasma generating means, and

wherein attach the droplet on the object to be processed by the transfer of the object to be processed and spraying the droplet from the droplet spraying means.

25. (Withdrawn) A semiconductor manufacturing apparatus according to claim 24, wherein the film formation treatment, the etching treatment or the attachment of the droplet is performed under atmospheric pressure or adjacent to atmospheric pressure.

26. (Withdrawn) A semiconductor manufacturing apparatus according to claim 24, wherein the means for transferring the object to be processed has a structure to transfer the object to be processed unidirectionally.

27. (Withdrawn) A semiconductor manufacturing apparatus according to claim 24, wherein the means for transferring the object to be processed has a structure to perform continuous or step-feed.

28. (Withdrawn) A semiconductor manufacturing apparatus according to claim 24, wherein a plurality of treatment selected from the film formation treatment, the etching treatment, the ashing treatment or the attachment treatment of the droplet are performed simultaneously.

29. (Previously Presented) A semiconductor manufacturing apparatus according to claim 1, wherein the first plasma treatment is performed by the first plasma generating device for forming a film over the object, etching the object, or ashing the object.

30. (Previously Presented) A semiconductor manufacturing apparatus according to claim 1, wherein the first plasma treatment is performed by the first plasma generating device while transferring the object and moving the first plasma generating device.

31. (Previously Presented) A semiconductor manufacturing apparatus according to claim 9, wherein the droplet is attached onto a surface of the object while transferring the object and moving the ink-jet device.

32. (Canceled)

33. (Previously Presented) A semiconductor manufacturing apparatus according to claim 19, wherein the plasma treatment is performed by the plasma generating device while transferring the object and moving the plasma generating device.

34. (Previously Presented) A semiconductor manufacturing apparatus according to claim 19, wherein the applying of the droplet is performed to a surface of the object under atmospheric pressure or approximate to atmospheric pressure.

35. (Previously Presented) A semiconductor manufacturing apparatus according to claim 19, wherein the first direction is a unidirection.

36. (Previously Presented)A semiconductor manufacturing apparatus according to claim 19, wherein the object is transferred continuously or with the use of step-feed.

37. (Previously Presented) A semiconductor manufacturing apparatus according to claim 19, wherein the droplet is an organic solvent containing resin or metal element.

38. (Previously Presented) A semiconductor manufacturing apparatus according to claim 19, wherein the droplet is attached onto a surface of the object while transferring the object and moving the ink-jet device.

39. (Previously Presented) A semiconductor manufacturing apparatus according to claim 9 further comprising a third plasma generating device for performing a third plasma treatment.

40. (Previously Presented) A semiconductor manufacturing apparatus according to claim 39, wherein the third plasma treatment is performed by the third plasma generating device for forming a film over the object, etching the object, or ashing the object.

41. (Previously Presented) A semiconductor manufacturing apparatus according to claim 1 wherein each of the first plasma generating device and the second plasma generating device comprises a first electrode and a second electrode for generating a plasma between the first electrode and the second electrode, and the first electrode and the second electrode have a nozzle-shaped opening.

42. (Previously Presented) A semiconductor manufacturing apparatus according to claim 9 wherein each of the first plasma generating device and the second plasma generating device comprises a first electrode and a second electrode for generating a plasma between the first electrode and the second electrode, and the first electrode and the second electrode have a nozzle-shaped opening.

43. (Previously Presented) A semiconductor manufacturing apparatus according to claim 9 wherein the ink-jet device comprises a nozzle provided with a hole for pushing out the droplet from the hole.

44. (Previously Presented) A semiconductor manufacturing apparatus according to claim 19 wherein the plasma generating device comprises a first electrode and a second electrode for generating a plasma between the first electrode and the second electrode, and the first electrode and the second electrode have a nozzle-shaped opening.

45. (Previously Presented) A semiconductor manufacturing apparatus according to claim 19 wherein the ink-jet device comprises a nozzle provided with a hole for pushing out the droplet from the hole.

46. (New) A semiconductor manufacturing apparatus according to claim 1 wherein the object comprises a glass.

47. (New) A semiconductor manufacturing apparatus according to claim 1 wherein the object comprises a quartz.

48. (New) A semiconductor manufacturing apparatus according to claim 1 wherein the object comprises a semiconductor.

49. (New) A semiconductor manufacturing apparatus according to claim 1 wherein the object comprises a metal.

50. (New) A semiconductor manufacturing apparatus according to claim 1 wherein the object comprises a ceramic.

51. (New) A semiconductor manufacturing apparatus according to claim 9 wherein the object comprises a glass.

52. (New) A semiconductor manufacturing apparatus according to claim 9 wherein the object comprises a quartz.

53. (New) A semiconductor manufacturing apparatus according to claim 9 wherein the object comprises a semiconductor.

54. (New) A semiconductor manufacturing apparatus according to claim 9 wherein the object comprises a metal.

55. (New) A semiconductor manufacturing apparatus according to claim 9 wherein the object comprises a ceramic.

56. (New) A semiconductor manufacturing apparatus according to claim 19 wherein the object comprises a glass.

57. (New) A semiconductor manufacturing apparatus according to claim 19 wherein the object comprises a quartz.

58. (New) A semiconductor manufacturing apparatus according to claim 19 wherein the object comprises a semiconductor.

59. (New) A semiconductor manufacturing apparatus according to claim 19 wherein the object comprises a metal.

60. (New) A semiconductor manufacturing apparatus according to claim 19 wherein the object comprises a ceramic.